







SN74LV6T17-EP SCLS981 - JANUARY 2024

# SN74LV6T17-EP Enhanced Product, Hex Schmitt-Trigger Buffer with Integrated **Translation**

#### 1 Features

- Wide operating range of 1.8V to 5.5V
- Single-supply voltage translator (refer to LVxT Enhanced Input Voltage):
  - Up translation:
    - 1.2V to 1.8V
    - 1.5V to 2.5V
    - 1.8V to 3.3V
    - 3.3V to 5.0V
  - Down translation:
    - 5.0V, 3.3V, 2.5V to 1.8V
    - 5.0V. 3.3V to 2.5V
    - 5.0V to 3.3V
- 5.5V tolerant input pins
- Supports standard pinouts
- Up to 150Mbps with 5V or 3.3V  $V_{CC}$
- Latch-up performance exceeds 250mA per JESD 17

## 2 Applications

- Enable or disable a digital signal
- Controlling an indicator LED
- Translation between communication modules and system controllers

## 3 Description

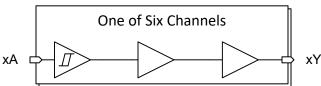
SN74LV6T17-EP device contains independent Buffers with Schmitt-trigger inputs. Each gate performs the Boolean function Y = A in positive logic. The output level is referenced to the supply voltage (V<sub>CC</sub>) and supports 1.8V, 2.5V, 3.3V, and 5V CMOS levels.

The input is designed with a lower threshold circuit to support up translation for lower voltage CMOS inputs (for example, 1.2V input to 1.8V output or 1.8V input to 3.3V output). In addition, the 5V tolerant input pins enable down translation (for example, 3.3V to 2.5V output).

#### **Package Information**

PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE <sup>(2)</sup>	BODY SIZE (NOM) <sup>(3)</sup>	
SN74LV6T17-EP	PW (TSSOP, 14)	5 mm × 6.4 mm	5 mm × 4.4 mm	

- For more information, see Section 13.
- The package size (length × width) is a nominal value and (2)includes pins, where applicable.
- (3)The body size (length × width) is a nominal value and does not include pins.



Simplified Logic Diagram (Positive Logic)



# **Table of Contents**

1 Features	7.4 Device Functional Modes1
2 Applications 1	8 Application and Implementation1
3 Description	8.1 Application Information1
4 Pin Configuration and Functions3	8.2 Typical Application1
5 Specifications4	9 Power Supply Recommendations1
5.1 Absolute Maximum Ratings4	10 Layout1
5.2 ESD Ratings4	10.1 Layout Guidelines1
5.3 Recommended Operating Conditions4	10.2 Layout Example1
5.4 Thermal Information4	11 Device and Documentation Support1
5.5 Electrical Characteristics5	11.1 Documentation Support1
5.6 Switching Characteristics6	11.2 Receiving Notification of Documentation Updates 1
5.7 Noise Characteristics6	11.3 Support Resources1
5.8 Typical Characteristics7	11.4 Trademarks1
6 Parameter Measurement Information10	11.5 Electrostatic Discharge Caution1
7 Detailed Description11	11.6 Glossary1
7.1 Overview11	12 Revision History1
7.2 Functional Block Diagram11	13 Mechanical, Packaging, and Orderable
7.3 Feature Description11	Information1



# **4 Pin Configuration and Functions**

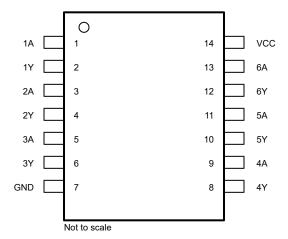


Figure 4-1. PW Package, 14-Pin TSSOP (Top View)

**Table 4-1. Pin Functions** 

PIN		TYPE <sup>(1)</sup>	DESCRIPTION
NAME	NO.	ITPE	DESCRIPTION
1A	1	I	Channel 1, Input A
1Y	2	0	Channel 1, Output Y
2A	3	1	Channel 2, Input A
2Y	4	0	Channel 2, Output Y
3A	5	1	Channel 3, Input A
3Y	6	0	Channel 3, Output Y
GND	7	G	Ground
4Y	8	0	Channel 4, Output Y
4A	9	I	Channel 4, Input A
5Y	10	0	Channel 5, Output Y
5A	11	1	Channel 5, Input A
6Y	12	0	Channel 6, Output Y
6A	13	I	Channel 6, Input A
V <sub>CC</sub>	14	Р	Positive Supply

<sup>(1)</sup> I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power.



## **5 Specifications**

## 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range		-0.5	7	V
VI	Input voltage range <sup>(2)</sup>				V
Vo	Voltage range applied to any outp	-0.5	7	V	
Vo	Output voltage range <sup>(2)</sup>			V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < -0.5V		-20	mA
I <sub>OK</sub>	Output clamp current	$V_{O}$ < -0.5V or $V_{O}$ > $V_{CC}$ +0.5V		±20	mA
Io	Continuous output current	V <sub>O</sub> = 0 to V <sub>CC</sub>		±25	mA
	Continuous output current through	n V <sub>CC</sub> or GND		±50	mA
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If briefly operating outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.

## 5.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2000	\/
V <sub>(ESD)</sub>	discharge	Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 <sup>(2)</sup>	±1000	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

## **5.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage	Supply voltage			V
VI	Input voltage	Input voltage		5.5	V
Vo	Output voltage		0	V <sub>CC</sub>	V
		V <sub>CC</sub> = 1.6V to 2V		±3	
Io	Output current	V <sub>CC</sub> = 2.25V to 2.75V		±7	mA
		V <sub>CC</sub> = 3.3V to 5.0V		±15	
Δt/Δν	Input transition rise or fall rate	V <sub>CC</sub> = 1.6V to 5.0V		20	ns/V
T <sub>A</sub>	Operating free-air temperature	Operating free-air temperature		125	°C

#### 5.4 Thermal Information

		SN74LV6T17-EP	
	THERMAL METRIC <sup>(1)</sup>	PW (TSSOP)	UNIT
		14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	147.7	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	77.4	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	90.9	°C/W

<sup>(2)</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



# **5.4 Thermal Information (continued)**

		SN74LV6T17-EP	
	THERMAL METRIC <sup>(1)</sup>	PW (TSSOP)	UNIT
		14 PINS	
$\Psi_{JT}$	Junction-to-top characterization parameter	27.2	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	90.2	°C/W
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

## 5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V	Т	<sub>A</sub> = 25°C		-55°	C to 125°C	;	UNIT	
PARAMETER	TEST CONDITIONS	V <sub>CC</sub>	MIN	TYP	MAX	MIN	TYP	MAX	UNII	
		1.65V to 2V	0.6		1.2	0.5		1.27		
	Positive-going input	2.25V to 2.75V	0.73		1.39	0.64		1.44	\/	
$V_{T+}$	threshold voltage	3V to 3.6V	0.88		1.59	0.80		1.63	V	
		4.5V to 5.5V	1.15		2.03	1.1		2.07		
		1.65V to 2V	0.225		0.685	0.185		0.755		
. ,	Negative-going input	2.25V to 2.75V	0.295		0.775	0.265		0.805	.,	
V <sub>T-</sub>	threshold voltage	3V to 3.6V	0.385		0.875	0.345		0.895	V	
		4.5V to 5.5V	0.535		1.075	0.495		1.085		
		1.65V to 2V	0.35		0.68	0.28		0.8		
A) (		2.25V to 2.75V	0.4		0.77	0.33		0.87	.,	
$\Delta V_{T}$	Hysteresis (V <sub>T+</sub> - V <sub>T-</sub> ) 3V to 3.6V 0.44 0.88 0.38	0.38		0.91	V					
		4.5V to 5.5V	0.53		1.2	0.51		1.4		
	I <sub>OH</sub> = -50μA	1.65V to 5.5V	V <sub>CC</sub> -0.1			V <sub>CC</sub> -0.1			V	
	I <sub>OH</sub> = -2mA	1.65V to 2V	1.28	1.7 (1)		1.21				
$V_{OH}$	I <sub>OH</sub> = -3mA	2.25V to 2.75V	2	2.4 <sup>(1)</sup>		1.93				
	I <sub>OH</sub> = -5.5mA	3V to 3.6V	2.6	3.08(1)		2.49				
	I <sub>OH</sub> = -8mA	4.5V to 5.5V	4.1	4.65 <sup>(1)</sup>		3.95				
	I <sub>OL</sub> = 50μA	1.65V to 5.5V			0.1			0.1		
	I <sub>OL</sub> = 2mA	1.65V to 2V		0.1 <sup>(1)</sup>	0.2			0.25		
$V_{OL}$	I <sub>OL</sub> = 3mA	2.25V to 2.75V		0.1 <sup>(1)</sup>	0.15			0.2	V	
	I <sub>OL</sub> = 5.5mA	3V to 3.6V		0.2(1)	0.2			0.25		
	I <sub>OL</sub> = 8mA	4.5V to 5.5V		0.3(1)	0.3			0.35		
lı	V <sub>I</sub> = 0V or V <sub>CC</sub>	0V to 5.5V			±0.1			±1	μA	
Icc	V <sub>I</sub> = 0V or V <sub>CC</sub> , I <sub>O</sub> = 0; open on loading	1.65V to 5.5V			2			20	μΑ	
۸۱	One input at 0.3V or 3.4V, other inputs at 0 or $V_{CC}$ , $I_{O} = 0$	5.5V			1.35			1.5	mA	
Δl <sub>CC</sub>	One input at 0.3V or 1.1V, other inputs at 0 or $V_{CC}$ , $I_{O} = 0$	1.8V			10			20	20 μΑ	
Cı	V <sub>I</sub> = V <sub>CC</sub> or GND	5V		4	10			10	pF	
Co	V <sub>O</sub> = V <sub>CC</sub> or GND	5V		3					pF	



## **5.5 Electrical Characteristics (continued)**

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V	TA	= 25°C		-55°(	C to 125°C	;	UNIT
FARAWETER	TEST CONDITIONS	V <sub>cc</sub>	MIN	TYP	MAX	MIN	TYP	MAX	ONII
C <sub>PD</sub>	No load, F = 1MHz	5V		14					pF

<sup>(1)</sup> Typical value at nearest nominal voltage (1.8V, 2.5V, 3.3V, and 5V)

## **5.6 Switching Characteristics**

over operating free-air temperature range; typical ratings measured at T<sub>A</sub> = 25°C (unless otherwise noted).

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	V <sub>CC</sub>	MIN	TYP	MAX	UNIT
t <sub>PHL</sub>	A	Υ	C <sub>L</sub> = 15pF	1.8V		15.6	40.1	ns
t <sub>PLH</sub>	A	Υ	C <sub>L</sub> = 15pF	1.8V		11.8	40.1	ns
t <sub>PHL</sub>	A	Y	C <sub>L</sub> = 50pF	1.8V		21.0	46.7	ns
t <sub>PLH</sub>	A	Y	C <sub>L</sub> = 50pF	1.8V		16.1	46.7	ns
t <sub>PHL</sub>	A	Y	C <sub>L</sub> = 15pF	2.5V		10.6	24.0	ns
t <sub>PLH</sub>	A	Υ	C <sub>L</sub> = 15pF	2.5V		7.1	24.0	ns
t <sub>PHL</sub>	A	Υ	C <sub>L</sub> = 50pF	2.5V		13.5	25.4	ns
t <sub>PLH</sub>	A	Υ	C <sub>L</sub> = 50pF	2.5V		10.1	25.4	ns
t <sub>PHL</sub>	A	Υ	C <sub>L</sub> = 15pF	3.3V		7.9	15.2	ns
t <sub>PLH</sub>	A	Υ	C <sub>L</sub> = 15pF	3.3V		5.4	13.8	ns
t <sub>PHL</sub>	A	Υ	C <sub>L</sub> = 50pF	3.3V		10.2	18.3	ns
t <sub>PLH</sub>	A	Υ	C <sub>L</sub> = 50pF	3.3V		7.8	16.0	ns
t <sub>PHL</sub>	A	Υ	C <sub>L</sub> = 15pF	5V		5.3	10.2	ns
t <sub>PLH</sub>	A	Υ	C <sub>L</sub> = 15pF	5V		4.2	9.9	ns
t <sub>PHL</sub>	A	Υ	C <sub>L</sub> = 50pF	5V		7.1	12.5	ns
t <sub>PLH</sub>	A	Υ	C <sub>L</sub> = 50pF	5V		5.8	11.5	ns

## **5.7 Noise Characteristics**

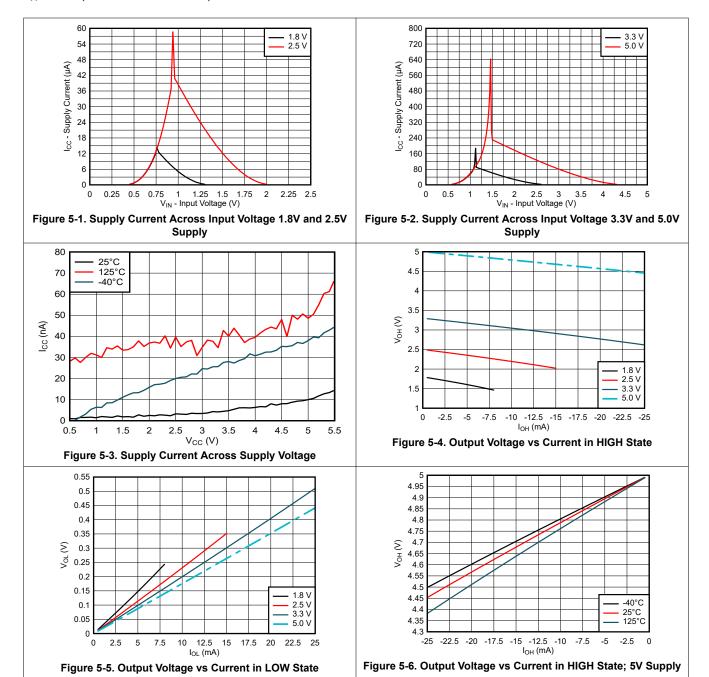
VCC = 5V, CL = 50pF, TA = 25°C

PARAMETER	DESCRIPTION	MIN	TYP	MAX	UNIT
V <sub>OL(P)</sub>	Quiet output, maximum dynamic V <sub>OL</sub>		1	1.2	V
V <sub>OL(V)</sub>	Quiet output, minimum dynamic V <sub>OL</sub>	-0.8	-0.3		V
V <sub>OH(V)</sub>	Quiet output, minimum dynamic V <sub>OH</sub>	4.4	5		V
V <sub>IH(D)</sub>	High-level dynamic input voltage	2.1			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.5	V



## **5.8 Typical Characteristics**

T<sub>A</sub> = 25°C (unless otherwise noted)





## 5.8 Typical Characteristics (continued)

T<sub>A</sub> = 25°C (unless otherwise noted)

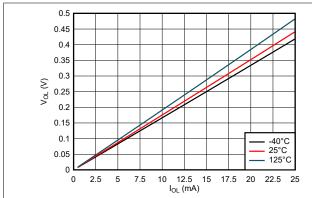


Figure 5-7. Output Voltage vs Current in LOW State; 5V Supply

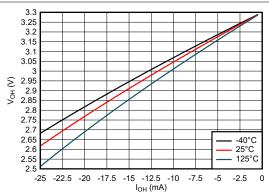


Figure 5-8. Output Voltage vs Current in HIGH State; 3.3V Supply

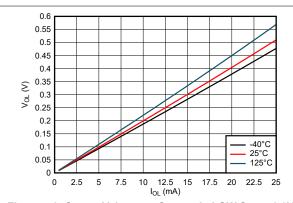


Figure 5-9. Output Voltage vs Current in LOW State; 3.3V Supply

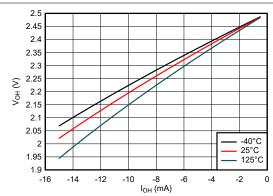
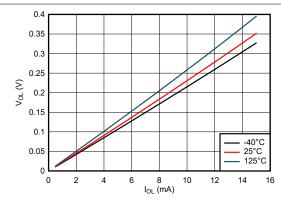


Figure 5-10. Output Voltage vs Current in HIGH State; 2.5V Supply





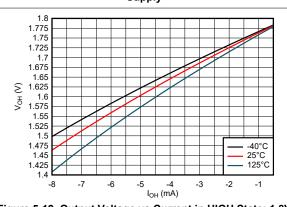
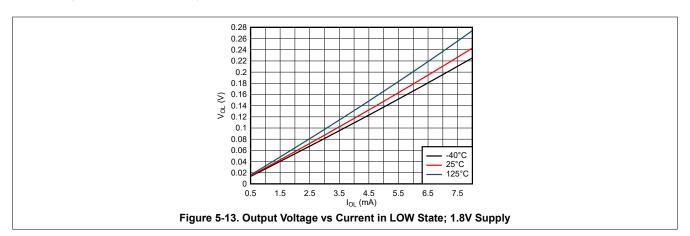


Figure 5-12. Output Voltage vs Current in HIGH State; 1.8V Supply



# **5.8 Typical Characteristics (continued)**

T<sub>A</sub> = 25°C (unless otherwise noted)



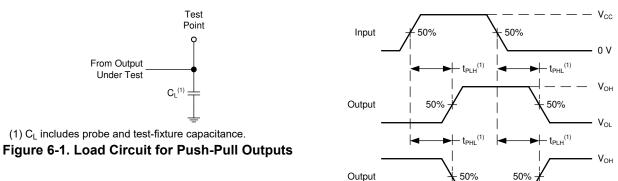


## **6 Parameter Measurement Information**

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics:  $PRR \le 1MHz$ ,  $Z_O = 50\Omega$ .

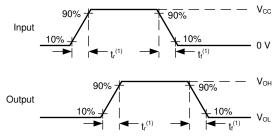
For clock inputs,  $f_{\text{max}}$  is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



(1) The greater between  $t_{PLH}$  and  $t_{PHL}$  is the same as  $t_{pd}$ .

Figure 6-2. Voltage Waveforms Propagation Delays



(1) The greater between  $t_{r}$  and  $t_{f}$  is the same as  $t_{t}$ .

Figure 6-3. Voltage Waveforms, Input and Output Transition Times



## 7 Detailed Description

#### 7.1 Overview

The SN74LV6T17-EP device contains six independent Buffers with Schmitt-trigger inputs. Each gate performs the Boolean function Y = A in positive logic. The output level is referenced to the supply voltage ( $V_{CC}$ ) and supports 1.8V, 2.5V, 3.3V, and 5V CMOS levels.

## 7.2 Functional Block Diagram



### 7.3 Feature Description

#### 7.3.1 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important to limit the output power of the device to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

#### 7.3.2 Clamp Diode Structure

The outputs to this device have both positive and negative clamping diodes, and the inputs to this device have negative clamping diodes only as shown in Figure 7-1.

#### **CAUTION**

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

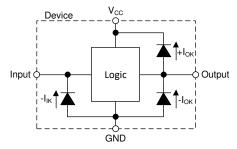


Figure 7-1. Electrical Placement of Clamping Diodes for Each Input and Output

## 7.3.3 CMOS Schmitt-Trigger Inputs

This device includes inputs with the Schmitt-trigger architecture. These inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics* table from the input to ground. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings* table, and the maximum input leakage current, given in the *Electrical Characteristics* table, using Ohm's law  $(R = V \div I)$ .

The Schmitt-trigger input architecture provides hysteresis as defined by  $\Delta V_T$  in the *Electrical Characteristics* table, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the inputs with slow transitioning signals will increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see Understanding Schmitt Triggers.

#### 7.3.4 LVxT Enhanced Input Voltage

The SN74LV6T17-EP belongs to TI's LVxT family of logic devices with integrated voltage level translation. This family of devices was designed with reduced input voltage thresholds to support up-translation, and inputs tolerant of signals with up to 5.5 V levels to support down-translation. The output voltage will always be referenced to the supply voltage (V<sub>CC</sub>), as described in the Electrical Characteristics table. For proper functionality, input signals must remain at or below the specified VIH(MIN) level for a HIGH input state, and at or below the specified V<sub>IL(MAX)</sub> for a LOW input state. Figure 7-2 shows the typical V<sub>IH</sub> and V<sub>IL</sub> levels for the LVxT family of devices, as well as the voltage levels for standard CMOS devices for comparison.

The inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the Electrical Characteristics. The worst case resistance is calculated with the maximum input voltage, given in the Absolute Maximum Ratings, and the maximum input leakage current, given in the Electrical Characteristics, using Ohm's law  $(R = V \div I)$ .

The inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the Recommended Operating Conditions table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in the Implications of Slow or Floating CMOS Inputs application report.

Do not leave inputs floating at any time during operation. Unused inputs must be terminated at V<sub>CC</sub> or GND. If a system will not be actively driving an input at all times, then a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; however, a 10-k $\Omega$  resistor is recommended and will typically meet all requirements.

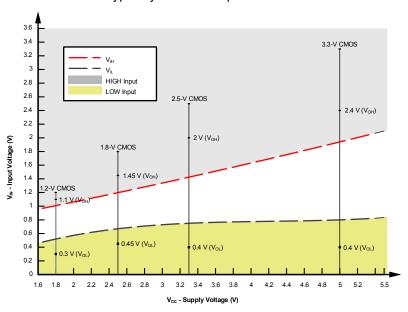


Figure 7-2. LVxT Input Voltage Levels

#### 7.3.4.1 Down Translation

Signals can be translated down using the SN74LV6T17-EP. The voltage applied at the V<sub>CC</sub> will determine the output voltage and the input thresholds as described in the Recommended Operating Conditions and Electrical Characteristics tables.



When connected to a high-impedance input, the output voltage will be approximately  $V_{CC}$  in the HIGH state, and 0V in the LOW state. As shown in Figure 7-2, ensure that the input signals in the HIGH state are between  $V_{IH(MIN)}$  and 5.5V, and input signals in the LOW state are lower than  $V_{IL(MAX)}$ .

As shown in Figure 7-3 for example, the standard CMOS inputs for devices operating at 5.0V, 3.3V or 2.5V can be down-translated to match 1.8V CMOS signals when operating from 1.8V  $V_{CC}$ .

Down Translation Combinations are as follows:

- 1.8V V<sub>CC</sub> Inputs from 2.5V, 3.3V, and 5.0V
- 2.5V V<sub>CC</sub> Inputs from 3.3V and 5.0V
- 3.3V V<sub>CC</sub> Inputs from 5.0V

#### 7.3.4.2 Up Translation

Input signals can be up translated using the SN74LV6T17-EP. The voltage applied at  $V_{CC}$  will determine the output voltage and the input thresholds as described in the *Recommended Operating Conditions* and *Electrical Characteristics* tables. When connected to a high-impedance input, the output voltage will be approximately  $V_{CC}$  in the HIGH state, and 0V in the LOW state.

The inputs have reduced thresholds that allow for input HIGH state levels which are much lower than standard values. For example, standard CMOS inputs for a device operating at a 5V supply will have a  $V_{IH(MIN)}$  of 3.5V. For the SN74LV6T17-EP,  $V_{IH(MIN)}$  with a 5V supply is only 2V, which would allow for up-translation from a typical 2.5V to 5V signals.

As shown in Figure 7-3, ensure that the input signals in the HIGH state are above  $V_{IH(MIN)}$  and input signals in the LOW state are lower than  $V_{IL(MAX)}$ .

Up Translation Combinations are as follows:

- 1.8V V<sub>CC</sub> Inputs from 1.2V
- 2.5V V<sub>CC</sub> Inputs from 1.8V
- 3.3V V<sub>CC</sub> Inputs from 1.8V and 2.5V
- 5.0V V<sub>CC</sub> Inputs from 2.5V and 3.3V

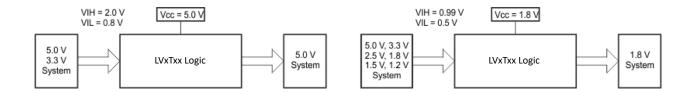


Figure 7-3. LVxT Up and Down Translation Example

#### 7.4 Device Functional Modes

Table 7-1 lists the functional modes of the SN74LV6T17-EP.

INPUT A<sup>(1)</sup>

H

L

OUTPUT
Y

H

H

Table 7-1. Function Table

(1) H = high voltage level, L = low voltage level, X = do not care, Z = high impedance



## 8 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 8.1 Application Information

The SN74LV6T17-EP can be used to drive signals over relatively long traces or transmission lines. In order to reduce ringing caused by impedance mismatches between the driver, transmission line, and receiver, a series damping resistor placed in series with the transmitter's output can be used. The figure in the Application Curve section shows the received signal with three separate resistor values. Just a small amount of resistance can make a significant impact on signal integrity in this type of application.

## 8.2 Typical Application

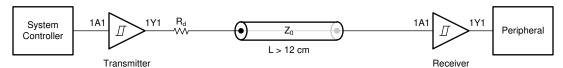


Figure 8-1. Typical Application Block Diagram

#### 8.2.1 Design Requirements

#### 8.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the Recommended Operating Conditions. The supply voltage sets the electrical characteristics of the device as described in the Electrical Characteristics section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74LV6T17-EP plus the maximum static supply current, I<sub>CC</sub>, listed in the *Electrical* Characteristics, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Be sure to not exceed the maximum total current through V<sub>CC</sub> listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74LV6T17-EP plus the maximum supply current, I<sub>CC</sub>, listed in the Electrical Characteristics, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Be sure to not exceed the maximum total current through GND listed in the Absolute Maximum Ratings.

The SN74LV6T17-EP can drive a load with a total capacitance less than or equal to 50pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50pF.

The SN74LV6T17-EP can drive a load with total resistance described by  $R_L \ge V_O / I_O$ , with the output voltage and current defined in the *Electrical Characteristics* table with V<sub>OH</sub> and V<sub>OL</sub>. When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the  $V_{CC}$  pin.

Total power consumption can be calculated using the information provided in the CMOS Power Consumption and Cpd Calculation application note.

Thermal increase can be calculated using the information provided in the Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices application note.



#### **CAUTION**

The maximum junction temperature,  $T_{J(max)}$  listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

#### 8.2.1.2 Input Considerations

Input signals must cross to be considered a logic LOW, and to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either  $V_{CC}$  or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74LV6T17-EP (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-k $\Omega$  resistor value is often used due to these factors.

Refer to the Feature Description section for additional information regarding the inputs for this device.

## 8.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the  $V_{OH}$  specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the  $V_{OL}$  specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V<sub>CC</sub> or ground.

Refer to the Feature Description section for additional information regarding the outputs for this device.



#### 8.2.2 Detailed Design Procedure

- Add a decoupling capacitor from V<sub>CC</sub> to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V<sub>CC</sub> and GND pins. An example layout is shown in the *Layout* section.
- Ensure the capacitive load at the output is ≤ 50pF. This is not a hard limit; it will, however, optimize performance. This can be accomplished by providing short, appropriately sized traces from the SN74LV6T17-EP to one or more of the receiving devices.
- 3. Ensure the resistive load at the output is larger than  $(V_{CC} / I_{O(max)}) \Omega$ , so that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in M $\Omega$ ; much larger than the minimum calculated previously.
- 4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, *CMOS Power Consumption and Cpd Calculation*.

## 8.2.3 Application Curves

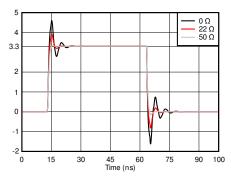


Figure 8-2. Simulated Signal Integrity at the Receiver With Different Damping Resistor (R<sub>d</sub>) Values

#### 9 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. A  $0.1\mu F$  capacitor is recommended for this device. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. The  $0.1\mu F$  and  $1\mu F$  capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in the following layout example.

# 10 Layout

#### 10.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices, inputs must never be left floating. In many cases, functions or parts of functions of digital logic devices are unused (for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used). Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or  $V_{\rm CC}$ , whichever makes more sense for the logic function or is more convenient.



## 10.2 Layout Example

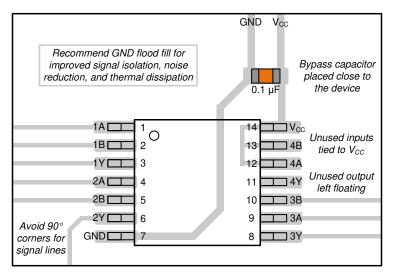


Figure 10-1. Example Layout for the SN74LV6T17-EP



## 11 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

## 11.1 Documentation Support

#### 11.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, CMOS Power Consumption and Cpd Calculation application note
- · Texas Instruments, Designing With Logic application note
- Texas Instruments, Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices application note
- Texas Instruments, Implications of Slow or Floating CMOS Inputs application note

## 11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

## 11.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 11.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

### 11.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 11.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

## 12 Revision History

DATE	REVSION	NOTES				
January 2024 *		Initial Release				

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com

.com 17-Oct-2025

#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		
SN74LV6T17PWREP	Active	Production	TSSOP (PW)   14	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	LV617EP
SN74LV6T17PWREP.A	Active	Production	TSSOP (PW)   14	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	LV617EP
V62/24623-01XE	Active	Production	TSSOP (PW)   14	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	See	LV617EP
								SN74LV6T17PWREP	

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### OTHER QUALIFIED VERSIONS OF SN74LV6T17-EP:

<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

# PACKAGE OPTION ADDENDUM

www.ti.com 17-Oct-2025

Catalog: SN74LV6T17

Automotive : SN74LV6T17-Q1

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 24-Jul-2025

## TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

	Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ĺ	SN74LV6T17PWREP	TSSOP	PW	14	3000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

**PACKAGE MATERIALS INFORMATION** 

www.ti.com 24-Jul-2025



## \*All dimensions are nominal

Device Package Type		Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
SN74LV6T17PWREP	TSSOP	PW	14	3000	353.0	353.0	32.0	



SMALL OUTLINE PACKAGE



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



#### IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you fully indemnify TI and its representatives against any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale, TI's General Quality Guidelines, or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products. Unless TI explicitly designates a product as custom or customer-specified, TI products are standard, catalog, general purpose devices.

TI objects to and rejects any additional or different terms you may propose.

Copyright © 2025, Texas Instruments Incorporated

Last updated 10/2025